

isc N-Channel MOSFET Transistor

45N20

FEATURES

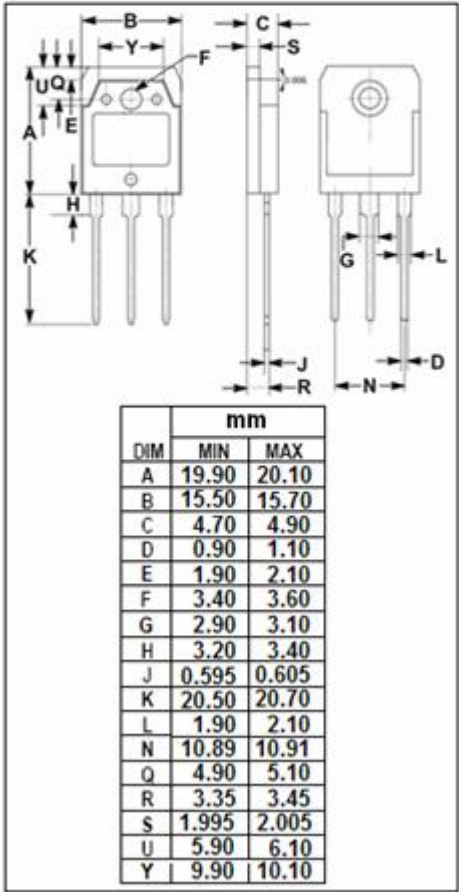
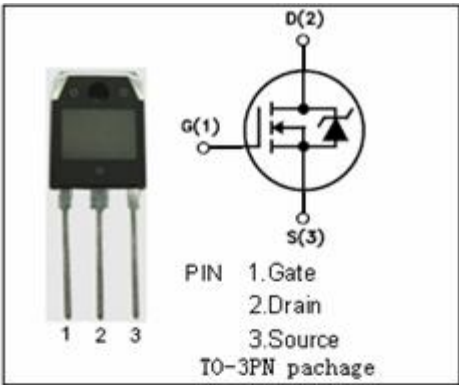
- Drain Current $I_D = 45A @ T_C = 25^{\circ}C$
- Drain Source Voltage
: $V_{DSS} = 200V (Min)$
- Static Drain-Source On-Resistance
: $R_{DS(on)} = 0.065 \Omega (Max)$
- Fast Switching

APPLICATIONS

- Switch mode power supply.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	200	V
V_{GS}	Gate-Source Voltage-Continuous	± 30	V
I_D	Drain Current-Continuous	45	A
P_D	Total Dissipation @ $T_C = 25^{\circ}C$	278	W
T_j	Max. Operating Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55~150	$^{\circ}C$



isc N-Channel MOSFET Transistor**45N20****• ELECTRICAL CHARACTERISTICS****T_C=25℃ unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D =250μA	200			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GE} ; I _D =250μA	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 22.5A			0.065	Ω
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±30V; V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =200V; V _{GS} = 0			200	μA